

## N-Channel 600V (D-S) Super Junction Power MOSFET With Fast Diode

PRODUCT SUMMARY		
V <sub>DS</sub> (V) at T <sub>J</sub> max.	600	
R <sub>DS(on)</sub> at 25 °C (Ω)	V <sub>GS</sub> = 10 V	0.120

### FEATURES

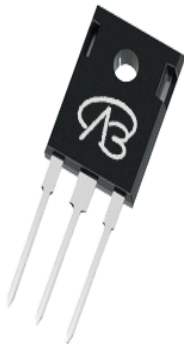
- Low figure-of-merit (FOM) R<sub>on</sub> x Q<sub>g</sub>
- Ultra-fast body diode
- Reduced switching and conduction losses
- Ultra low gate charge (Q<sub>g</sub>)
- Avalanche energy rated (UIS)



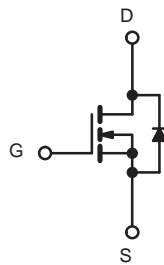
### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial

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Top View



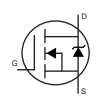
N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	600	V	
Gate-Source Voltage	V <sub>GS</sub>	± 30		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	25	A
		T <sub>C</sub> = 100 °C	15	
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	75		
Linear Derating Factor		1.67	W/°C	
Single Pulse Avalanche Energy <sup>b</sup>	E <sub>AS</sub>	980	mJ	
Maximum Power Dissipation	P <sub>D</sub>	155	W	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Drain-Source Voltage Slope	dV/dt	50	V/ns	
Reverse Diode dV/dt <sup>d</sup>				15
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s	260	°C	

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- V<sub>DD</sub> = 100 V, starting T<sub>J</sub> = 25 °C, L = 28.2 mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 7.5 A.
- 1.6 mm from case.
- I<sub>SD</sub> ≤ I<sub>D</sub>, dI/dt = 100 A/μs, starting T<sub>J</sub> = 25 °C.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.57	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$		600	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	0.70	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.5	-	4.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	$\pm 1$	$\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=600\text{V}, V_{GS}=0\text{V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	100	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 8.5\text{ A}$	-	0.120	-	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 8.5\text{ A}$		-	5.6	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V},$ $V_{DS} = 100\text{ V},$ $f = 1\text{ MHz}$		-	2800	-	pF
Output Capacitance	$C_{oss}$			-	80	-	
Reverse Transfer Capacitance	$C_{rss}$			-	4	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$		-	63	-	
Effective Output Capacitance, Time Related <sup>b</sup>	$C_{o(tr)}$			-	213	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 8\text{ A}, V_{DS} = 520\text{ V}$	-	5.8	-	nC
Gate-Source Charge	$Q_{gs}$			-	15	-	
Gate-Drain Charge	$Q_{gd}$			-	1.9	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520\text{ V}, I_D = 8\text{ A},$ $V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	18	25	ns
Rise Time	$t_r$			-	24	55	
Turn-Off Delay Time	$t_{d(off)}$			-	8.0	-	
Fall Time	$t_f$			-	1.2	-	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}, \text{ open drain}$		-	0.8	-	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p-n junction diode 		-	-	25	A
Pulsed Diode Forward Current	$I_{SM}$			-	-	75	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 8\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.5	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 8\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}, V_R = 400\text{ V}$		-	475	-	ns
Reverse Recovery Charge	$Q_{rr}$			-	5.8	-	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$			-	30	-	A

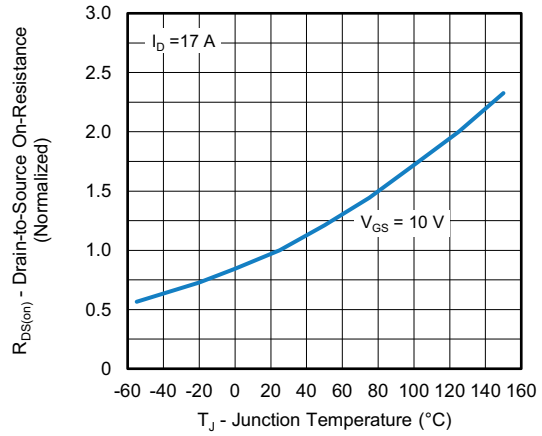
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .
- b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Fig. 1 - Typical Output Characteristics**



**Fig. 4 - Normalized On-Resistance vs. Temperature**



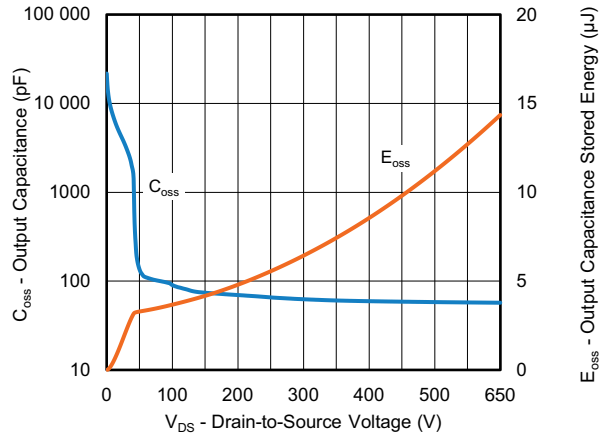
**Fig. 2 - Typical Output Characteristics**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 6 - C<sub>oss</sub> and E<sub>oss</sub> vs. V<sub>DS</sub>**



Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage



Fig. 10 - Maximum Drain Current vs. Case Temperature



Fig. 8 - Typical Source-Drain Diode Forward Voltage

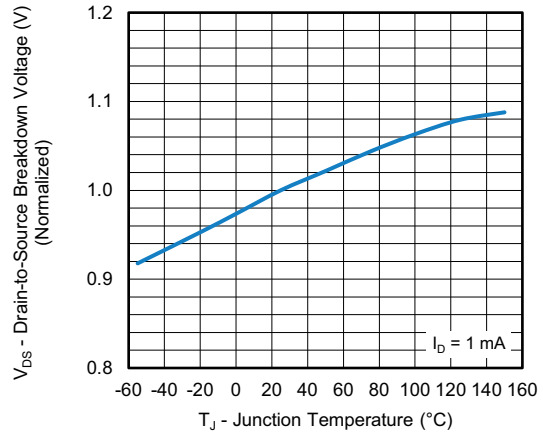


Fig. 11 - Temperature vs. Drain-to-Source Voltage



Fig. 9 - Maximum Safe Operating Area

**Note**

a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

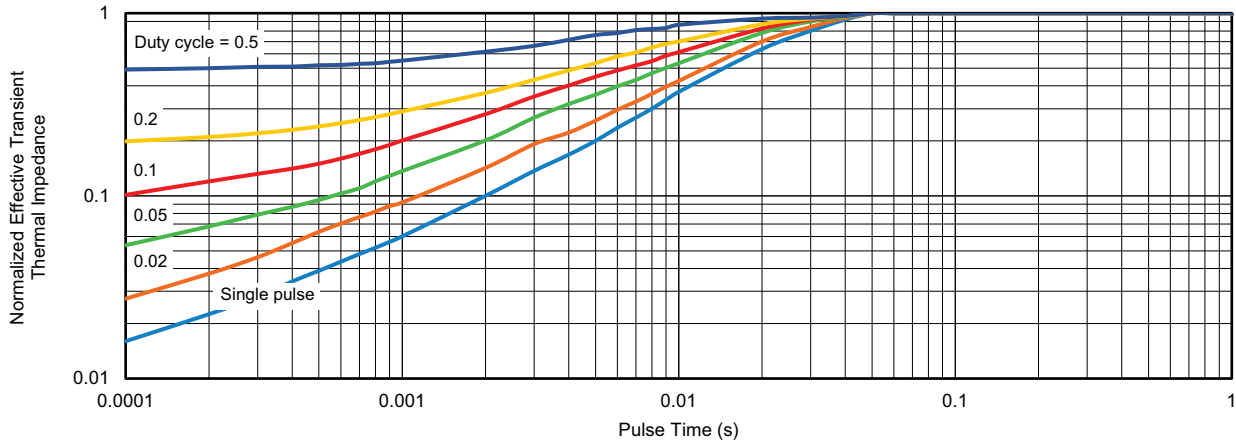


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

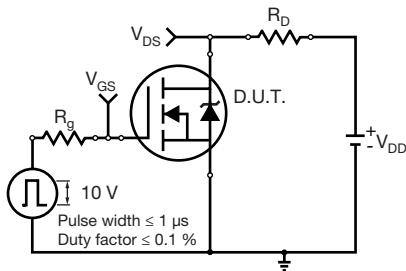


Fig. 13 - Switching Time Test Circuit



Fig. 16 - Unclamped Inductive Waveforms



Fig. 14 - Switching Time Waveforms



Fig. 17 - Basic Gate Charge Waveform

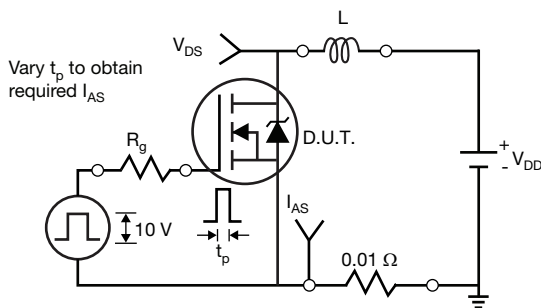


Fig. 15 - Unclamped Inductive Test Circuit

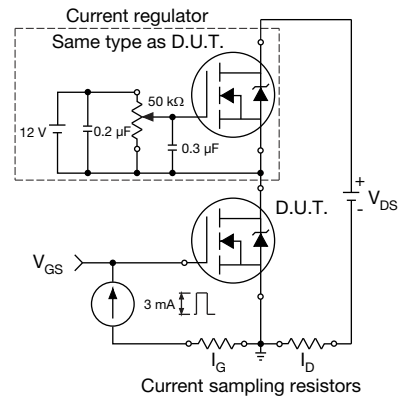


Fig. 18 - Gate Charge Test Circuit

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DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.70	5.31	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.41	0.065	0.095
b4	2.59	3.43	0.102	0.135
c	0.61 BSC		0.024 BSC	
D	20.80	21.46	0.819	0.845
D1	3.68	5.49	0.145	0.216
(e)	5.46 BSC		0.215 BSC	
E	15.49	16.26	0.610	0.640
L	19.81	20.32	0.780	0.800
L1	4.06	4.50	0.160	0.177
$\varnothing p$	3.51	3.66	0.138	0.144

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